

METHOD FOR FORMING A JUNCTION REGION OF A SEMICONDUCTOR DEVICE

BACKGROUND OF THE INVENTION

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1.FIELD OF THE INVENTION

The invention relates to a method for forming a junction region of a semiconductor device, more particularly to the method for forming a junction region of a PMOS semiconductor device.

2.DESRIPTION OF THE PRIOR ART

15 As semiconductor devices, such as complementary metal-oxide-semiconductor devices, become highly integrated, the area occupied by the devices shrinks, as well as the design rule. With advances in semiconductor technology, the dimensions of the integrated circuit (IC) devices have shrunk to the deep sub-micron region, some problems are incurred due to the process of scaling down.

25 With the progress of semiconductor elements, the manufacturing of semiconductor elements is more and more precise and therefore, the depth distribution of

impurity atoms is more and more precise. In generally,
an ion implanting method is used to precisely control the
depth and concentration distributions of the impurity
atoms. In the process of ion implanting, the impurity
5 atoms with a form of charged ions are accelerated to have
energy and then they can collide the silicon wafer directly
to enter into a proper position in the crystal lattices.
Therefore, the depth distribution of the ions can be
controlled by the energy of the ion, while the dose of the
10 impurities can be controlled by the implanting time and
current of the ion beam.

In the prior art, the charged ions as an ion beam with
certain energy is implanted into a silicon wafer by using
15 an ion implanter. Then, an annealing process required
for activating impurities and recovering damage, thereby
causing a redistribution of the implanted ions and the
occurrence of a transient enhance diffusion (TED)
phenomenon. Consequently, it is difficult to form ultra
20 shallow junctions by traditional ion-implantation.
Moreover, when the line width of the devices is required to
be reduced to be below 90nm, and area of each section,
including source and drain, in the metal oxide
semiconductor (MOS) must also be reduced, and thus the
25 diffusing depth of the junction must be controlled severely
for reducing the short channel effect and the punch-

through effect.

As device scaling for the 90nm technology node and beyond, ultra shallow and low sheet resistance source/drain extensions (SDE) are required to suppress the short channel effect and to obtain high current drivability. Recent study has been shown towards carbon implantation as an approach for fabricating ultra shallow junctions by low energy implantation, carbon atom act to sink silicon interstitials, thereby reducing enhanced dopant diffusion. However, introduction of carbon by ion implantation can lead to higher leakage current in p-n junctions and lower throughput in production. Accordingly, it is one of considerable issues on the application of carbon implantation.

SUMMARY OF THE INVENTION

In accordance with the background of the above-mentioned invention, the traditional ion-implantation method can not form the needed ultra shallow junctions. One objective of the present invention is to provide a method for forming a junction region of a semiconductor device. Employing carbon-containing plasma treatment controls the region of the junction. Therefore, after the subsequent thermal process, the property of the element

can be retained. A lower depth junction is acquired, and the diffusion in the horizontal direction is suppressed.

Another objective of the present invention is to
5 provide a method for forming a junction region of a semiconductor device by employing carbon-containing plasma treatment, herein carbon-containing plasma treatment produces carbon ions to penetrate near the surface of the wafer substrate. The damage to the wafer
10 substrate is reduced. This is beneficial to the re-crystallization in the thermal process and does not lead to higher leakage current in p-n junctions just like ion implantation.

15 In accordance with the present invention, a method for forming a junction region of a semiconductor device is disclosed. The steps of the method include providing a semiconductor substrate. A gate structure is formed on the semiconductor substrate. A dopant is implanted into
20 the semiconductor substrate to form the junction region. An insulator layer is formed on the gate structure and the semiconductor substrate. A carbon-containing plasma treatment is performed to the insulator layer. A spacer is formed on a side-wall of the gate structure and the
25 dopant is implanted into the semiconductor substrate to form a source/drain region next to the junction region.

A heat treatment is performed to the semiconductor substrate.

BRIEF DESCRIPTION OF THE DRAWINGS

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The present invention can be best understood through the following description and accompanying drawings wherein:

10 FIGS. 1A-1F are a series of cross-sectional schematic diagrams of the embodiment of the present invention.

DESCRIPTION OF THE PREFERRED EMBODIMENT

15 There is shown a representative portion of a semiconductor structure of the present invention in enlarged, cross-sections of the two dimensional views at several stages of fabrication. The drawings are not necessarily to scale, as the thickness of the various layers
20 are shown for clarify of illustration and should not be interpreted in a limiting sense. Accordingly, these regions will have dimensions, including length, width and depth, when fabricated in an actual device.

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One embodiment of the present invention is depicted in FIGS.1A-1F. First referring to FIG.1A, a semiconductor substrate 10, such as a silicon substrate, is provided for the formation of p-type and/or n-type MOS devices. In one embodiment, some devices or structures (not shown) may be included in the semiconductor substrate 10, such as some doped wells or isolation devices. Next, an oxide layer and a conductive layer are sequentially formed on the semiconductor substrate 10. The oxide layer and the conductive layer are then patterned and etched by any suitable methods. Thus, a gate structure, which consists of the gate oxide layer 20 and the gate electrode 21, is formed on the semiconductor substrate 10. Alternatively, for a specified design, an

offset spacer (not shown) may be formed on the side-wall of the gate structure.

Next, for some PMOS devices in an embodiment, a p-type implantation is performed for the aforesaid structure. In the embodiment, the dopant 11 of the group III, such as boron, is implanted into the semiconductor substrate 10 for the formation of a source/drain extension junction region. In a preferred embodiment, the implantation of low energy boron 11 with pre-amorphization implantation of germanium is implemented with energy on the order of 1 to 10 keV. Accordingly, the application of the present invention is not only used to form PMOS devices but also used to form NMOS devices.

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Referring to FIG.1B, after the formation of a source/drain extension junction region 15 (having a thickness about less than 400 angstroms), an insulator layer 25, such as an oxide liner, is conformally deposited on the gate structure and the semiconductor substrate 10. Next, one of the features of the present invention, carbon-containing plasma 13 treatment is performed to incorporate carbon atoms 14 into the insulator layer 25 and carbon atoms 14 can diffuse into the source/drain extension junction region 15 during subsequent heat treatment, such as a furnace annealing treatment and a

rapid thermal annealing treatment for recovering damage of the source/drain region. The proceeding temperature of the subsequent heat treatment is about 500 to 1200°C. In this embodiment, without limitation, the rapid thermal
5 annealing treatment whose proceeding temperature is about 900 to 1200 °C for recovering damage of the source/drain region 18 during subsequent processes is used as the subsequent heat treatment. Carbon atoms
14 can sink silicon interstitials to retard boron diffusion
10 so as to make the source/drain extension junction region 15, which also be called as the ultra shallow junction, be stable. Besides, in this embodiment, without limitation, carbon dioxide is used as the source of the carbon-containing plasma. Preferably for the carbon-containing
15 plasma the power level is on the order of 0.1 to 0.5 w/cm², and the concentration of carbon atoms in the ultra shallow junction is around above 1e19/cm³.

A dielectric liner layer, such as a nitride liner, is first
20 conformally formed on the insulator layer 25. Then, the dielectric liner layer 27 and the insulator layer 25 are etched to form a spacer 29 formed on the side-wall of the gate structure, depicted in FIG.1C. Next, p-type ion
25 implantation 17 is carried out to the semiconductor substrate 10 so as to form the source /drain region 18, depicted in FIG.1D. Next, one step of a annealing

treatment, such as a rapid thermal annealing treatment, with a condition at about 900 to 1200°C for about 0 to 30 seconds (dwell time) is carried out to recover damage of the source /drain region 18 and activate the dosage without too much impurity diffusion. Besides, the other of the features of the present invention, the rapid thermal annealing treatment for recovering damage of the source/drain region 18 can also make carbon atoms 14 incorporated within the insulator layer 25 diffuse into the source/drain extension junction region 15 to reduce boron diffusion, as shown in FIG.1D.

Referring to FIG.1E, Co metal 30 is deposited on the gate electrode 21 and the source/drain region 18 about 100 angstroms. First CoSi compound is formed on the gate electrode 21 and the source/drain region 18 by annealing in low temperature and the un-reacted Co metal on the gate structure and the source/drain region is removed. Finally, a second thermal annealing is provided to form CoSi₂ compound 31, as shown in FIG.1F.

The method of the present invention can retard the boron diffusion in horizontal and vertical direction and assure the dopant within the ultra shallow junctions not redistribution due to next heat treatment or thermal cycle by the carbon atoms which diffuse into the semiconductor

substrate adjusted by the treating time of the carbon-containing plasma and the treating power of the aforesaid plasma.

5 Above said preferred embodiment is only used to illustrate the present invention, not intended to limit the scope thereof. Many modifications of the preferred embodiment can be made without departing from the spirit of the present invention.